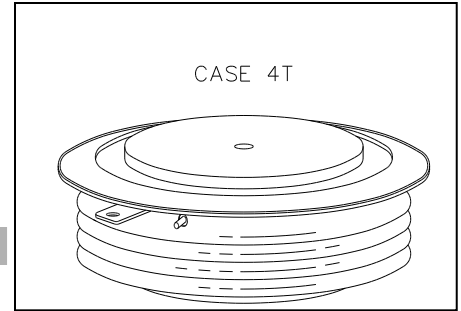


## HIGH POWER THYRISTOR FOR PHASE CONTROL APPLICATIONS

### Features:

- . All Diffused Structure
- . Center Amplifying Gate Configuration
- . Blocking capability up to 4200 volts
- . Guaranteed Maximum Turn-Off Time
- . High dV/dt Capability
- . Pressure Assembled Device

DCR1020SF60~65



## ELECTRICAL CHARACTERISTICS AND RATINGS

### Blocking - Off State

|               |               |               |
|---------------|---------------|---------------|
| $V_{RRM}$ (1) | $V_{DRM}$ (1) | $V_{RSM}$ (1) |
| 6000~6500     | 6000~6500     | 6100~6600     |

$V_{RRM}$  = Repetitive peak reverse voltage

$V_{DRM}$  = Repetitive peak off state voltage

$V_{RSM}$  = Non repetitive peak reverse voltage (2)

|   |                     |                     |
|---|---------------------|---------------------|
| Repetitive peak reverse leakage and off state | $I_{RRM} / I_{DRM}$ | 25 mA<br>150 mA (3) |
| Critical rate of voltage rise                 | dV/dt (4)           | 1000 V/μsec         |

### Notes:

All ratings are specified for  $T_j=25^\circ\text{C}$  unless otherwise stated.

(1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range  $-40$  to  $+125^\circ\text{C}$ .

(2) 10 msec. max. pulse width

(3) Maximum value for  $T_j = 125^\circ\text{C}$ .

(4) Minimum value for linear and exponential waveshape to 80% rated  $V_{DRM}$ . Gate open.  $T_j = 125^\circ\text{C}$ .

(5) Non-repetitive value.

(6) The value of di/dt is established in accordance with EIA/NIMA Standard RS-397, Section 5-2-2-6. The value defined would be in addition to that obtained from a snubber circuit, comprising a 0.2 μF capacitor and 20 ohms resistance in parallel with the thyristor under test.

### Conducting - on state

| Parameter  | Symbol      | Min. | Max.               | Typ. | Units  | Conditions  |
|--|-------------|------|--------------------|------|--------|---|
| Average value of on-state current                | $I_{T(AV)}$ |      | 640                |      | A      | Sinewave, 180° conduction, $T_c=60^\circ\text{C}$                                   |
| RMS value of on-state current                    | $I_{TRMS}$  |      | 1005               |      | A      | Nominal value   |
| Peak one cPSTCLe surge (non repetitive) current  | $I_{TSM}$   |      | -                  |      | KA     | 8.3 msec (60Hz), sinusoidal wave-shape, 180° conduction, $T_j = 125^\circ\text{C}$  |
|  |             |      | 8.5                |      | KA     | 10.0 msec (50Hz), sinusoidal wave-shape, 180° conduction, $T_j = 125^\circ\text{C}$ |
| I square t                                       | $I^2t$      |      | $0.36 \times 10^6$ |      | $A^2s$ | 8.3 msec and 10.0 msec  |
| Latching current                                 | $I_L$       |      | 600                |      | mA     | $V_D = 24\text{ V}$ ; $R_L = 12\text{ ohms}$  |
| Holding current                                  | $I_H$       |      | 200                |      | mA     | $V_D = 24\text{ V}$ ; $I = 2.5\text{ A}$  |
| Peak on-state voltage                            | $V_{TM}$    |      | 3.6                |      | V      | $I_{TM} = 1800\text{ A}$ ; Duty cPSTCLe $\leq 0.01\%$ ; $T_j = 25^\circ\text{C}$    |
| Critical rate of rise of on-state current (5, 6) | di/dt       |      | -                  |      | A/μs   | Switching from $V_{DRM} \leq 1000\text{ V}$ , non-repetitive                        |
| Critical rate of rise of on-state current (6)    | di/dt       |      | 100                |      | A/μs   | Switching from $V_{DRM} \leq 1000\text{ V}$   |

## ELECTRICAL CHARACTERISTICS AND RATINGS

### Gating

| Parameter                                  | Symbol      | Min. | Max.          | Typ. | Units          | Conditions   |
|--|-------------|------|---------------|------|----------------|--|
| Peak gate power dissipation                | $P_{GM}$    |      | 150           |      | W              | $t_p = 40 \mu s$   |
| Average gate power dissipation             | $P_{G(AV)}$ |      | 5             |      | W              |  |
| Peak gate current                          | $I_{GM}$    |      | -             |      | A              |  |
| Gate current required to trigger all units | $I_{GT}$    |      | -<br>300<br>- |      | mA<br>mA<br>mA | $V_D = 6 V; R_L = 3 \text{ ohms}; T_j = -40^\circ C$<br>$V_D = 6 V; R_L = 3 \text{ ohms}; T_j = +25^\circ C$<br>$V_D = 6 V; R_L = 3 \text{ ohms}; T_j = +125^\circ C$                        |
| Gate voltage required to trigger all units | $V_{GT}$    |      | -<br>3.0<br>- |      | V<br>V<br>V    | $V_D = 6 V; R_L = 3 \text{ ohms}; T_j = -40^\circ C$<br>$V_D = 6 V; R_L = 3 \text{ ohms}; T_j = 0-125^\circ C$<br>$V_D = \text{Rated } V_{DRM}; R_L = 1000 \text{ ohms}; T_j = +125^\circ C$ |
| Peak negative voltage                      | $V_{GRM}$   |      | 5             |      | V              |  |

### Dynamic

| Parameter                           | Symbol   | Min. | Max. | Typ. | Units   | Conditions  |
|-------------------------------------|----------|------|------|------|---------|---|
| Delay time                          | $t_d$    |      | -    | 0.5  | $\mu s$ | $I_{TM} = 50 A; V_D = \text{Rated } V_{DRM}$<br>Gate pulse: $V_G = 20 V; R_G = 20 \text{ ohms}; t_r = 0.1 \mu s; t_p = 20 \mu s$  |
| Turn-off time (with $V_R = -50 V$ ) | $t_q$    |      | -    | 600  | $\mu s$ | $I_{TM} = 1000 A; di/dt = 25 A/\mu s;$<br>$V_R \geq -50 V; \text{Re-applied } dV/dt = 20 V/\mu s \text{ linear to } 80\% V_{DRM}; V_G = 0;$<br>$T_j = 125^\circ C; \text{Duty cPSTCle} \geq 0.01\%$ |
| Reverse recovery charge             | $Q_{rr}$ |      | *    |      | $\mu C$ | $I_{TM} = 1000 A; di/dt = 25 A/\mu s;$<br>$V_R \geq -50 V$  |

\* For guaranteed max. value, contact factory.

## THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS

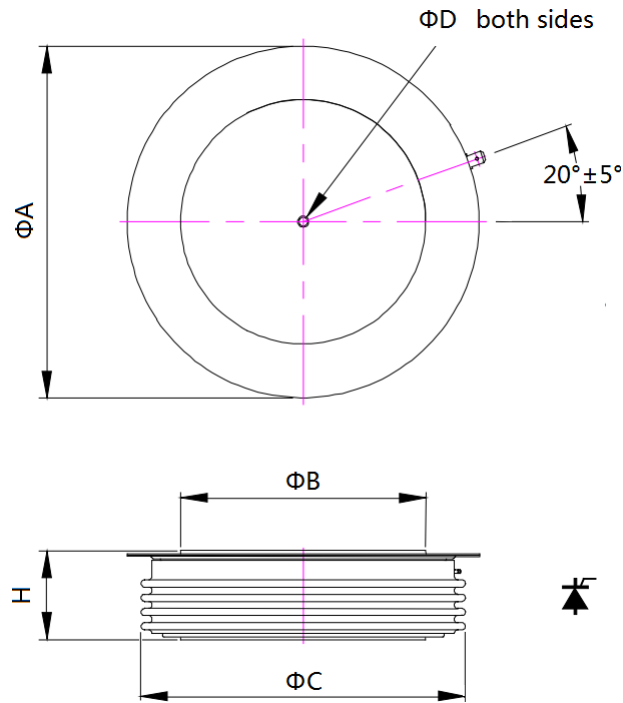
| Parameter                             | Symbol            | Min. | Max.           | Typ. | Units        | Conditions                                     |
|---------------------------------------|-------------------|------|----------------|------|--------------|--|
| Operating temperature                 | $T_j$             | -40  | +125           |      | $^\circ C$   |  |
| Storage temperature                   | $T_{stg}$         | -40  | +125           |      | $^\circ C$   |  |
| Thermal resistance - junction to case | $R_{\theta(j-c)}$ |      | 0.022<br>0.052 |      | $^\circ C/W$ | Double sided cooled<br>Single sided cooled     |
| Thermal resistance - case to sink     | $R_{\theta(c-s)}$ |      | 0.004<br>0.008 |      | $^\circ C/W$ | Double sided cooled *<br>Single sided cooled * |
| Thermal resistance - junction to sink | $R_{\theta(j-s)}$ |      | -<br>-         |      | $^\circ C/W$ | Double sided cooled *<br>Single sided cooled * |
| Mounting force                        | P                 | 18   | 22             |      | kN           |  |
| Weight                                | W                 |      |                |      | g            |  |

\* Mounting surfaces smooth, flat and greased



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CASE OUTLINE AND DIMENSIONS



| Sym | A  | B  | C  | D     | H    |
|-----|----|----|----|-------|------|
| mm  | 75 | 47 | 66 | 3.5x3 | 26±1 |